

TiO ₂ Film using Sputter#2 (PM#2)						
Power (W)	Gas Flow-rate (sccm)		Deposition Rate (Å/min)	Refractive Index	Stress (MPa)*	Buffered HF Etch Rate (Å/min)
	Ar	O ₂				
2300	20	10	118	2.365	132	240
*: Stress in tensile						

Note: Prior to the TiO₂ deposition, do an Ar-plasma clean of the Ti target with a 2000 W power and 20 SCCM Ar flow-rate for 20 minutes, then, a TiO₂ film coating (the same parameters, shown in the above table) of PM#2 chamber for 10 minutes.